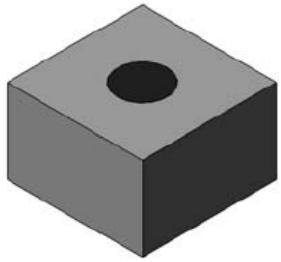
JANHCB1N5711, JANKCB1N5711

Schottky Barrier Diode Die

Rev. V1

Features

- Qualified to MIL-PRF-19500/444
- Compatible With All Wire Bonding And Die Attach Techniques with The Exception Of Solder Reflow
- Silicon Dioxide Passivated
- Ideal For Space, Military, & Other High Reliability Applications
- Available In Commercial Version As CD5711



Electrical Characteristics (T_A = +25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Reverse Breakdown Voltage	I_R = 10 µA dc	$V_{(BR)1}$	V dc	70	—
Reverse Breakdown Voltage	T_A = -55 °C I_R = 10 µA dc	$V_{(BR)2}$	V dc	70	—
Forward Voltage	I_F = 1 mA dc	V_{F1}	V dc	—	0.410
Forward Voltage	I_F = 15 mA dc	V_{F2}	V dc	—	1.0
Forward Voltage	T_A = -55°C I_F = 1 mA dc	V_{F3}	V dc	—	.55
Forward Voltage	T_A = -55°C I_F = 15 mA dc	V_{F4}	V dc	—	1.0
Reverse Current	V_R = 50 V dc	I_{R1}	nA dc	—	200
Reverse Current	T_A = +150°C V_R = 50 V dc	I_{R2}	µA dc	—	200
Capacitance	V_R = 0, f = 1 MHz, V_{sig} = 50 mV (pk)	C	pF	—	2.0
Effective Carrier Lifetime	(See DESC Drawing C68001)	t_{CL}	ps		100

Absolute Maximum Ratings (T_A = +25°C unless otherwise specified)

Ratings	Symbol	Value
Working Voltage	V_{RWM}	50 V (pk)
Reverse Current	I_{O1}	33 mA dc
Reverse Current	I_{O2}	5 mA dc
Operating & Storage Temperature Range	T_J, T_{STG}	-65°C to +150°C

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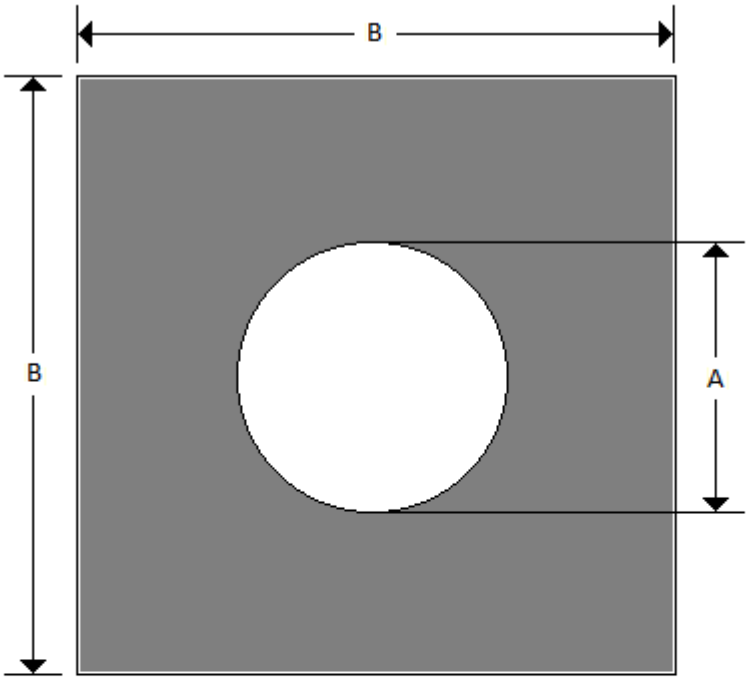
Outline Drawing (Die)



1N5711 Dimensions				
Ltr	Inches		Millimeters	
	Min	Max	Min	Max
A	.004	.006	.102	.152
B	.011	.013	.279	.330

NOTES:
1. Dimensions are in inches. Millimeters are given for general information only.
2. The physical characteristics of the die are:
   Metallization:
   Top (anode): Al.
   Back (cathode): Au.
   Al thickness: 14,000 Å minimum.
   Gold thickness: 5,600 Å minimum.
   Chip thickness: .008 inch (.203 mm) ± .002 inch (± .051 mm).
3. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.